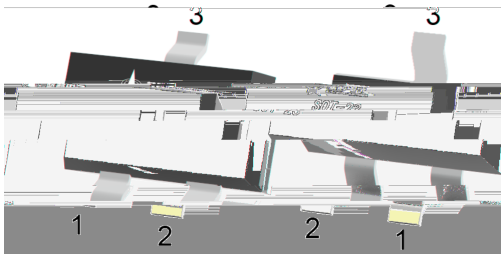
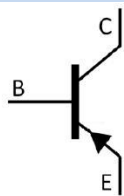


Silicon PNP transistor in a SOT-23 Plastic Package.

Complementary pair with S8050MG,HF Product.

Power amplifier applications.



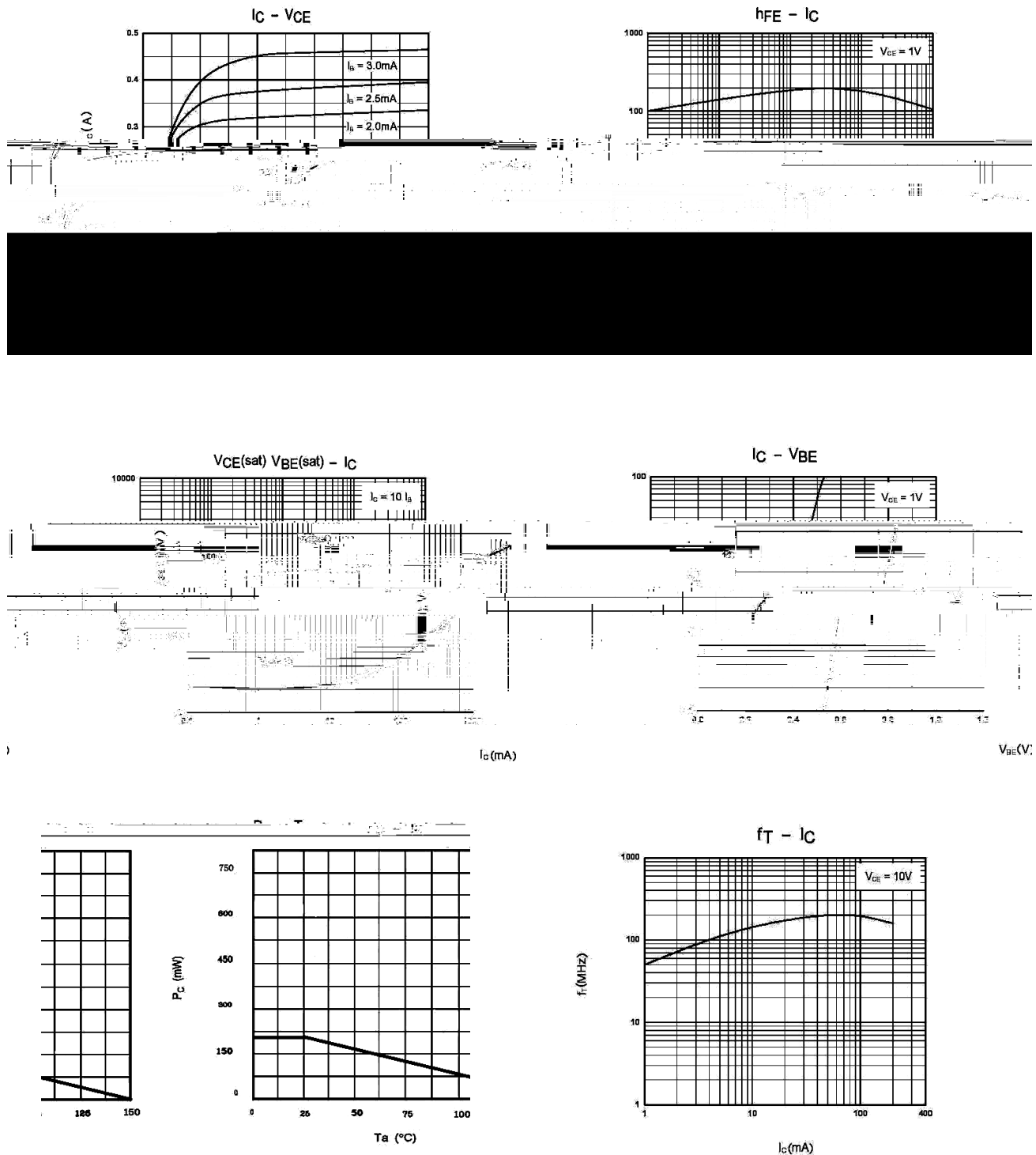
PIN1 Base PIN 2 Emitter PIN 3 Collector

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	85 160	120 200	160 300
Marking	GY4B	GY4C	GY4D

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

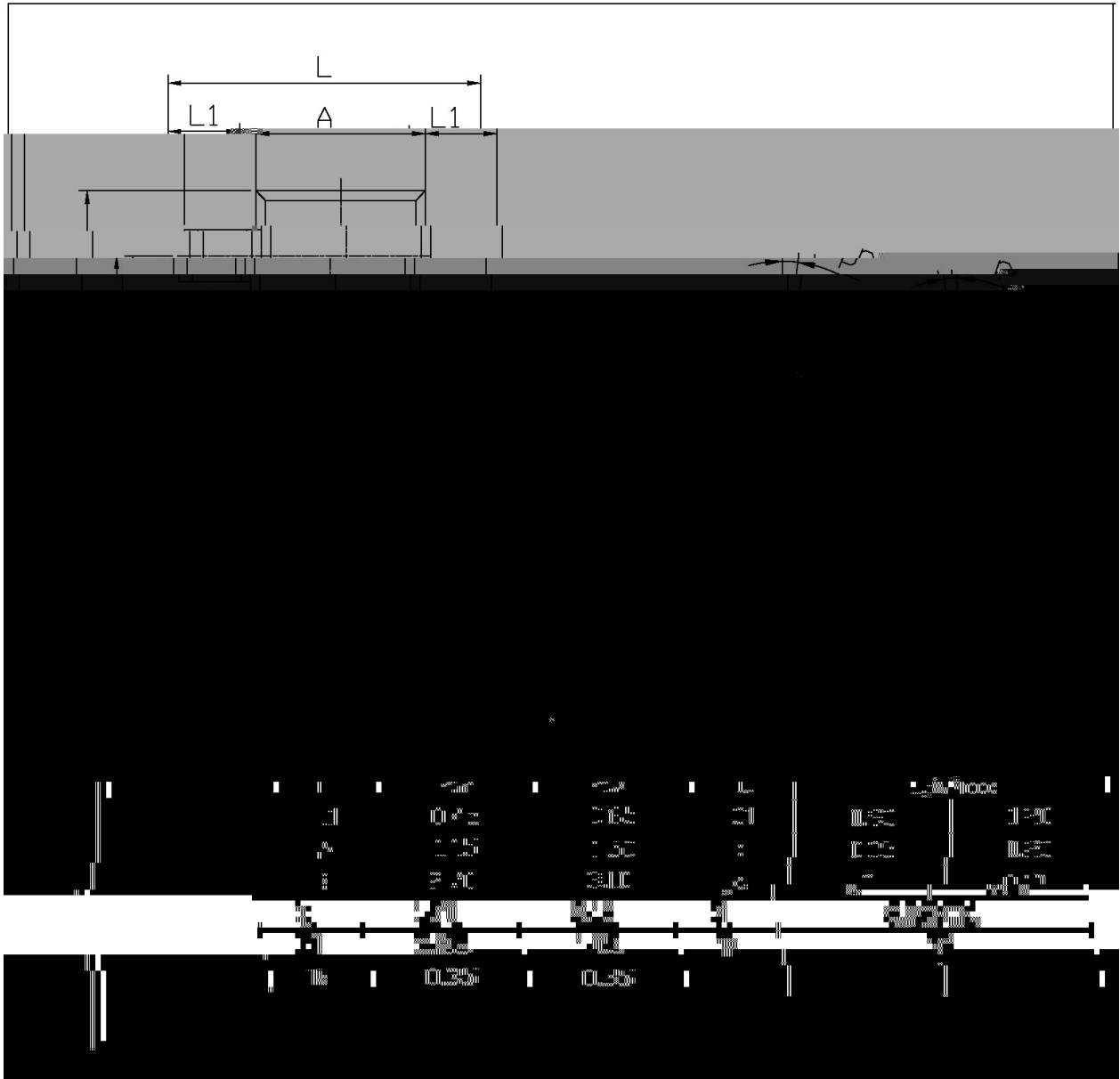
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-0.1mA$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-2.0mA$ $I_B=0$	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-0.1mA$ $I_C=0$	-6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-35V$ $I_E=0$			-0.1	A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	85		300	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-500mA$	40			
	$h_{FE(3)}$	$V_{CE}=-1.0V$ $I_C=-5.0mA$	45			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$		-0.28	-0.6	V

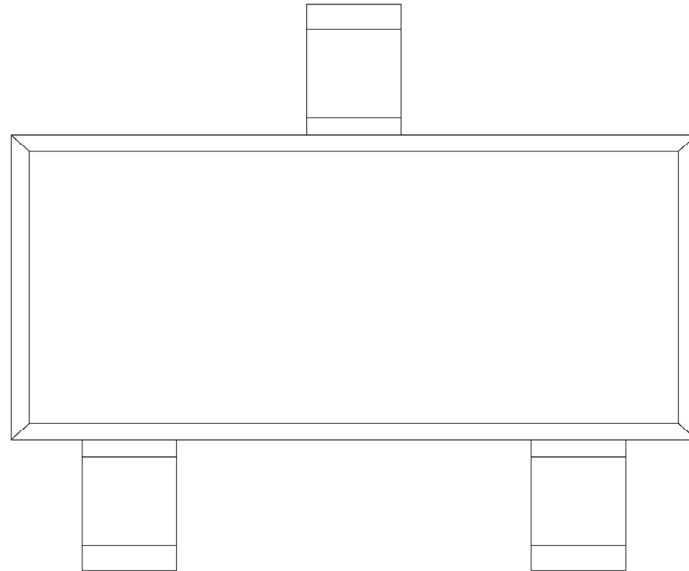
Base-Emitter Saturation Voltage V

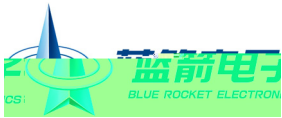


SOT-23

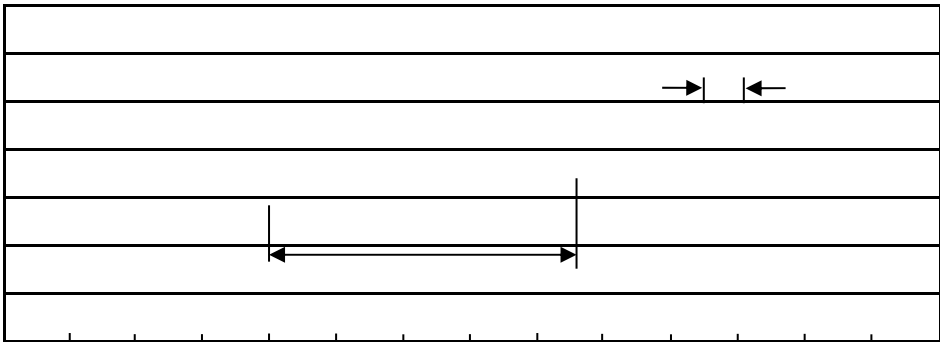
单位: 元







Temperature Profile for IR Reflow Soldering(Pb-Free)



- Note:
- 1

150 180

60 90sec;

2

245 5

5 0.5sec;
- 3
- 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205